L Numbe	r Hits	Search Text	I DD	(m
-	7	y\$1branch and corner same (etch\$4 or	DB USPAT;	Time stamp
		mask\$4 or photo\$1resist)	US-PGPUB;	2003/03/10 10:38
		procedure of proce	EPO; JPO;	
1			DERWENT;	
1	1		IBM TDB	
-	22	corner near8 (etch\$4 or mask\$4 or	USPAT;	2003/03/10 10:58
ļ		photo\$1resist) near5 sharp\$4 same	US-PGPUB;	2003/03/10 10:58
ļ	ļ	isotropic and 438/\$4.ccls.	EPO; JPO;	İ
İ			DERWENT;	ł
			IBM TDB	
_	3	1 1 1	USPAT;	2003/03/10 11:00
		same (etch\$\$ or mask\$4 or pattern\$4)	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
l _	3	y\$1branch\$3 and (sharp\$4 near5 corner)	IBM_TDB	
		same (etch\$4 or mask\$4 or pattern\$4)	USPAT;	2003/03/10 11:01
		same (etchy4 or mask\$4 or pattern\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
-	9	leon.in. and etch\$4 same corner\$3	USPAT:	2003/03/10 11:01
			US-PGPUB;	2003/03/10 11:01
			EPO; JPO;	
			DERWENT;	
		. Of the second	IBM TDB	•
-	1	1 - Coling of all a	USPAT;	2003/03/10 11:41
		(cmp or polish\$4)	US-PGPUB;	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2
			EPO; JPO;	
			DERWENT;	
1_	1 3		IBM_TDB	
-	3	y\$1branch\$3 and (etch\$4 near6 corner)	USPAT;	2003/03/10 11:54
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	99	(etch\$4 near6 corner) near10 isotropic\$4	IBM_TDB	0000 (00 (10 00 00
		and 438\$5.ccls.	USPAT; US-PGPUB;	2003/03/10 13:17
		10040100101	EPO; JPO;	
			DERWENT;	1
			IBM TDB	
-	14	(sharpen\$3 near6 corner) same etch\$4	USPAT;	2003/03/10 13:30
			US-PGPUB;	1 20100
			EPO; JPO;	
İ	Ì		DERWENT;	
		(.)	IBM_TDB	
_	9	(sharpen\$3 near6 corner) and 438\$5.ccls.	USPAT;	2003/03/10 13:32
			US-PGPUB;	
			EPO; JPO;	j
]		DERWENT; IBM TDB	
-	2	5521422.pn.	USPAT;	2003/03/14 10:12
	-		US-PGPUB;	2003/03/14 10:12
] [EPO; JPO;	
			DERWENT;	[
]		IBM TDB	
_	33	leon.in. and francisco.in.	USPAT;	2003/03/14 10:17
			US-PGPUB;	
			EPO; JPO;	
]		DERWENT;	
		100/05	IBM_TDB	
-	18	438/25.ccls. and corner\$4	USPAT;	2003/03/14 10:34
	į (US-PGPUB;	}
	j l		EPO; JPO;	
			DERWENT;	
_	14	438/25.ccls. and sharp\$5	IBM_TDB	2002/02/14 12 25
	1 1	100/20.0015. and snarpso	USPAT;	2003/03/14 10:36
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
	13.00.0			

		· ,			
	_	73	y\$1branch\$4 same (etch\$4 or mask\$4) and waveguide	USPAT; US-PGPUB;	2003/03/14 10:39
				EPO; JPO; DERWENT;	
	Í _	64		IBM_TDB	
	İ	04	y\$1branch\$4 same etch\$\$	USPAT;	2003/03/18 16:44
				US-PGPUB; EPO; JPO;	
				DERWENT;	
	_	64	y\$1branch\$4 same etch\$4	IBM_TDB	
		04	yarbrancha4 same etch\$4	USPAT;	2003/03/18 17:01
				US-PGPUB; EPO; JPO;	
				DERWENT;	
	_	6	y\$1branch\$4 same etch\$4 and (chemical	IBM_TDB	
			near3 polish\$4 or cmp)	USPAT; US-PGPUB;	2003/03/18 16:46
			process, or comp,	EPO; JPO;	
				DERWENT;	
	_	33	LEON.in. and FRANCISCO.in.	IBM_TDB	
			DEGN. III. and FRANCISCO. III.	USPAT; US-PGPUB;	2003/03/18 17:02
				EPO; JPO;	
				DERWENT;	
_		. 86	LEON near2 FRANCISCO	IBM_TDB =	
			DEGN NEGIZ FRANCISCO	USPAT; US-PGPUB;	2003/03/18 17:02
				EPO; JPO;	
				DERWENT;	
	_	21	(LEON near2 FRANCISCO).in.	IBM_TDB	0000/00/10 15
			(250) Hears Francisco). III.	USPAT; US-PGPUB;	2003/03/18 17:03
				EPO; JPO;	
				DERWENT;	
	_	2	((LEON near2 FRANCISCO).in. or (everett	IBM_TDB USPAT;	2002/02/10 17 04
1		_	near2 wang).in.) and grat\$4	US-PGPUB;	2003/03/18 17:04
				EPO; JPO;	
			·	DERWENT;	
	_	22	(LEON near2 FRANCISCO).in. or (everett	<pre>IBM_TDB USPAT;</pre>	2003/03/18 17:09
			near2 wang).in.	US-PGPUB;	2003/03/16 17:09
	1			EPO; JPO;	
				DERWENT;	
	- [47	diffract\$4 near2 grat\$4 same etch\$4 same	<pre>IBM_TDB USPAT;</pre>	2003/03/19 10:12
			monit\$5	US-PGPUB;	2003/03/13 10.12
				EPO; JPO;	
	ĺ			DERWENT; IBM TDB	
	-	55	grat\$4 same etch\$4 near10 monit\$5	USPAT;	2003/03/19 10:49
				US-PGPUB;	
				EPO; JPO;	
				DERWENT; IBM TDB	
	-	11	trench near4 fill\$4 same (cmp or chemical	USPAT;	2003/03/19 11:47
			near2 (polish\$4 or planar\$5)) same	US-PGPUB;	
	1		deposit\$4 and 438/\$4.ccls. and (photonic or mems or y\$1branch)	EPO; JPO;	
			or mems or yerbranch)	DERWENT; IBM TDB	
1	-	70	trench near4 fill\$4 near4 (nitride) same	USPĀT;	2003/03/19 12:18
	ł		(cmp or chemical near2 (polish\$4 or	US-PGPUB;	
			planar\$5)) same deposit\$4 and 438/\$4.ccls.	EPO; JPO; DERWENT;	
				IBM TDB	
-	-	5	trench near4 fill\$4 same (cmp or chemical	USPĀT;	2003/03/19 12:20
			near2 (polish\$4 or planar\$5)) same deposit\$4 same core and 438/\$4.ccls.	US-PGPUB;	
		[depositer same core and 438/\$4.CCIs.	EPO; JPO; DERWENT;	
L				IBM TDB	

-	2	trench near4 fill\$4 same (cmp or chemical	USPAT;	2003/03/19 12:25
	Į	near2 (polish\$4 or planar\$5)) same	US-PGPUB;	12.23
		deposit\$4 and 438/\$4.ccls. and (core same	EPO; JPO;	
		clad\$4)	DERWENT;	
			IBM_TDB	
-	11	trench near4 fill\$4 same (cmp or chemical	USPAT;	2003/03/19 12:30
1		near2 (polish\$4 or planar\$5)) same	US-PGPUB;	
		deposit\$4 and 438/\$4.ccls. and waveguide	EPO; JPO;	ł
i			DERWENT;	
_	1 0	filled pand within	IBM_TDB	İ
	٥	1ogr :rcrrgc game (cmb of chemical		2003/03/19 12:32
		near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and waveguide	US-PGPUB;	
		depositor and asovar.ceis. and waveguide	EPO; JPO;	
			DERWENT;	
-	128	fill\$4 near4 nitride same (cmp or chemical	IBM_TDB USPAT;	2002/02/10 10 17
		near2 (polish\$4 or planar\$5)) same	US-PGPUB;	2003/03/19 12:47
		deposit\$4 and 438/\$4.ccls.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	to demic fomb of chemical heats	USPAT;	2003/03/19 12:48
		(polish\$4 or planar\$5)) same deposit\$4 and	US-PGPUB;	1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -
		438/\$4.ccls. and y\$1branch\$3	EPO; JPO;	
			DERWENT;	
İ _	22	5/1104	IBM_TDB	=: • ()
	- 33	fill\$4 same (cmp or chemical near2	USPAT;	2003/03/19 12:49
ŀ		(polish\$4 or planar\$5)) same deposit\$4 and	US-PGPUB;	}
	į	438/\$4.ccls. and mems	EPO; JPO;	
			DERWENT;	
_	23	("4307180" "4786954" "4849344"	IBM_TDB	
		"5173439" "5272117" "5296392"	USPAT	2003/03/19 13:21
		"5297082" "5346587" "5433794"		
1		"5436488" "5459096" "5492858"		
		"5506168" "5516625" "5516721"		
		"5521422" "5677233" "5683932"		
		"5712185" "5801083" "5811346"		
		"5834358" "5960297").PN.		
-	27	trench near2 isolation near2 structure	USPAT;	2003/03/19 15:15
		same oxide near5 overly\$4	US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
1_	1	RCA\$1A near10 HF	IBM_TDB	
	1	RCASIA Heallo Hr	USPAT;	2003/03/19 15:16
i			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	1	RCA\$1A same HF	USPAT;	2003/03/19 15:16
			US-PGPUB;	2003/03/13 13:10
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	12	RCA\$1A	USPĀT;	2003/03/19 15:17
			US-PGPUB;	1
	[[EPO; JPO;	
			DERWENT;	į l
-		/UD10 /-1 40	IBM_TDB	
-	26	(HF near10 (clean\$3 or pre\$1clean\$3) same	USPAT;	2003/03/19 17:06
		trench) and (STI or shallow\$1trench)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	2	5521422.pn.	IBM_TDB USPAT;	2003/03/19 16:07
	i -1		US-PGPUB;	2003/03/19 16:07
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	75	isotropic same corner same etch\$4 same	1	
		sharp\$4	USPAT; US-PGPUB;	2003/03/19 16:08
			EPO; JPO;	
			DERWENT;	
_	84	(STI or shallow\$1trench) and MEMS	IBM_TDB USPAT;	2003/03/19 17:06
			US-PGPUB;	2003/03/19 17:06
			EPO; JPO;	
			DERWENT;	
-	9	(STI or shallow\$ltrench) same MEMS	IBM_TDB USPAT;	2003/03/19 17:06
			US-PGPUB;	2003/03/13 17.00
	İ		EPO; JPO;	
1	1		DERWENT; IBM TDB	
-	1	(STI or shallow\$1trench) same MEMS!	USPAT;	2003/03/19 17:07
	Í		US-PGPUB;	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
			EPO; JPO;	
			DERWENT; IBM TDB	
-	5	(STI or shallow\$1trench) and MEMS!	USPAT;	2003/03/19 17:08
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM-TDB	
-	27	(STI or shallow\$1trench) and waveguide	USPĀT;	2003/03/19 17:11
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	82	(STI or shallow\$1trench or shallow adj trench) and waveguide	USPAT;	2003/03/20 09:53
		crencity and waveguide	US-PGPUB; EPO; JPO;	
İ			DERWENT;	
_	17	(CMT on shall-will and the shall are the sha	IBM_TDB	
_	1	(STI or shallow\$1trench or shallow adj trench) same waveguide	USPAT;	2003/03/19 17:11
1		bane waveguide	US-PGPUB; EPO; JPO;	
			DERWENT;	
-		(STI or shallow\$1trench or shallow adj	IBM_TDB	2002/02/12 17 22
		trench) and waveguide and (y\$1branch or y	USPAT; US-PGPUB;	2003/03/19 17:33
		adj branch)	EPO; JPO;	
	1		DERWENT;	
-	5	(STI or shallow\$1trench or shallow adj	IBM_TDB USPAT;	2003/03/20 10:35
		trench) same (mems! or	US-PGPUB;	2003/03/20 10.33
		microelectromechanical)	EPO; JPO;	
			DERWENT; IBM TDB	
-	105	corner same etch\$4 near4 wet and optical\$4	USPAT;	2003/03/20 10:57
]	•	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	92	corner same etch\$4 near4 wet same sharp\$5	USPĀT;	2003/03/20 11:10
İ			US-PGPUB;	
			EPO; JPO; DERWENT;	
	1		IBM_TDB	
-	75	etch\$4 near4 (wet or isotropic) and y adj branch\$4	USPĀT;	2003/03/20 12:45
	1	DI GIIOII 94	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	41	otobed nound (v.)	IBM_TDB	
	41	etch\$4 near4 (wet or isotropic) same (dry or anisotropic) and y adj branch\$4	USPAT;	2003/03/20 11:18
			US-PGPUB; EPO; JPO;	
			DERWENT;	
	L		IBM TDB	

-	1	y adj branch\$4.ti. and (wet near4 etch\$4)	USPAT; US-PGPUB;	2003/03/20 11:19
			EPO; JPO; DERWENT; IBM TDB	
		y adj branch\$4.ti. and 438\$5.ccls.	USPAT; US-PGPUB; EPO; JPO;	2003/03/20 11:21
_	61	u odi humahût waxas () a	DERWENT; IBM_TDB	
	01	y adj branch\$4 near15 (mask\$4 or pattern\$4)	USPAT; US-PGPUB; EPO; JPO;	2003/03/20 13:34
-	30	y adj branch\$4 near35 etch\$5	DERWENT; IBM_TDB USPAT;	2003/03/20 11:58
			US-PGPUB; EPO; JPO; DERWENT;	2003/03/20 11.56
-	6	y adj branch\$4 near35 sharp\$4	IBM_TDB USPAT;	2003/03/20 12:42
			US-PGPUB; EPO; JPO; DERWENT;	
-	6	y adj branch\$4 near35 clean\$4	IBM_TDB USPAT; US-PGPUB;	2003/03/20 12:44
			EPO; JPO; DERWENT; IBM TDB	
_	53	corner and y adj branch\$4 and optical	USPAT; US-PGPUB; EPO; JPO;	2003/03/20 12:46
-	6	corner same etch\$4 and y adj branch\$4 and	DERWENT; IBM_TDB USPAT;	2003/03/20 12:50
		optical	US-PGPUB; EPO; JPO; DERWENT;	2000,03,20 12.50
_	68	corner near10 etch\$4 near5 (wet or isotropic) same (photoresist or resist or	IBM_TDB USPAT; US-PGPUB;	2003/03/20 12:58
		mask\$4) and 438/\$5.ccls.	EPO; JPO; DERWENT;	
_	10	y adj branch\$4 near15 (photoresist or resist)	IBM_TDB USPAT; US-PGPUB;	2003/03/20 13:42
			EPO; JPO; DERWENT; IBM_TDB	
	10	y adj branch\$4 same corner	USPĀT; US-PGPUB; EPO; JPO;	2003/03/20 13:37
-	30	y adj branch\$4 near35 etch\$4	DERWENT; IBM_TDB USPAT;	2003/03/20 14:19
			US-PGPUB; EPO; JPO; DERWENT;	
-	84	y adj branch\$4 near5 waveguide and etch\$4 same cladding	IBM_TDB USPAT; US-PGPUB;	2003/03/20 14:23
			EPO; JPO; DERWENT; IBM TDB	
-	12	y adj branch\$4 near5 waveguide and etch\$4 same cladding and (chemical near2 mechanical or cmp)	USPAT; US-PGPUB; EPO; JPO;	2003/03/20 14:52
			DERWENT; IBM_TDB	

-	32	cladding near20 etch\$4 near4 wet same core	USPAT: 2003	3/03/20 15:04
		and waveguide	US-PGPUB;	77 0 37 20 13.04
1			EPO; JPO;	
1			DERWENT;	
_	84	(shallow add though an att)	IBM_TDB	
	"	(shallow adj trench or sti) and waveguide		3/03/20 15:05
			US-PGPUB;	
			EPO; JPO;	
]			DERWENT; IBM TDB	
-	17	(shallow adj trench or sti) same waveguide		/03/20 16:06
		,	US-PGPUB;	703720 10.00
			EPO; JPO;	
ļ			DERWENT;	
]	2.2		IBM TDB	
i	33	waveguide near10 y adj branch\$4 same	USPAT; 2003	/03/20 16:10
		etch\$4	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	